

S/N 09/944981

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: Walter Lindsay

Serial No.: 09/944981

Group Art Unit: 2812

Filed: August 30, 2001

Docket: 1303.021US1

CRYSTALLINE OR AMOPHOUS MEDIUM-K GATE OXIDES, Y2O3 AND Gd2O3

INFORMATION DISCLOSURE STATEMENT

MS Amendment

Commissioner for Patents

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In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

06/22/2004 GWORDF1 00000151 09944981

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By their Representatives,

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Date

6-18-04

By

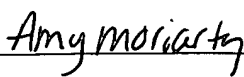


David C. Peterson

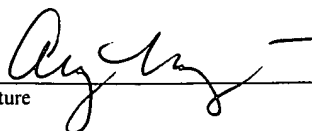
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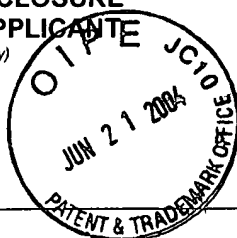
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Application Number	09/944981
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Examiner Name	Lindsay, Walter

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Attorney Docket No: 1303.021US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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	US-2001/0009695 A1	07/26/2001	Saanila, Ville A., et al.	427	255.39	01/18/2001
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	US-2003/0052358	03/20/2003	Weimer, Ronald A.	257	310	10/25/2002
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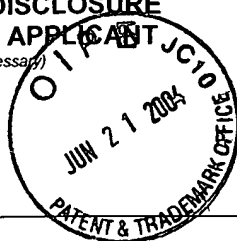
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Examiner Name	Lindsay, Walter

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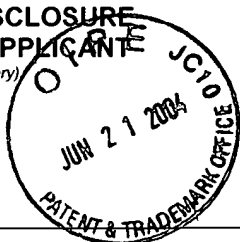
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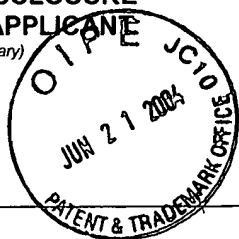
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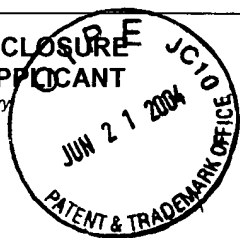
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		AARIK, JAAN, et al., "Atomic layer growth of epitaxial TiO/sub 2/ thin films from TiCl/sub 4/ and H/sub 2/O on alpha -Al/sub 2/O/sub 3/ substrates", <u>Journal of Crystal Growth</u> , 242(1-2), (2002), 189-198	
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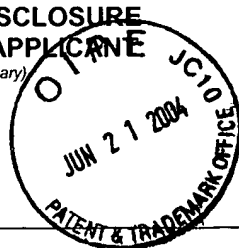
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Sheet 6 of 12

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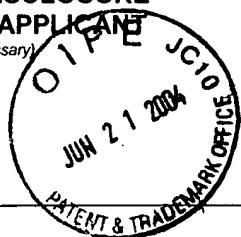
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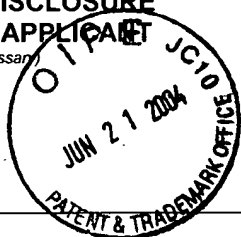
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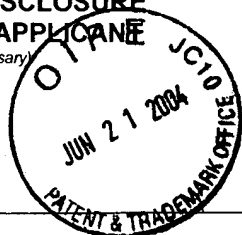
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